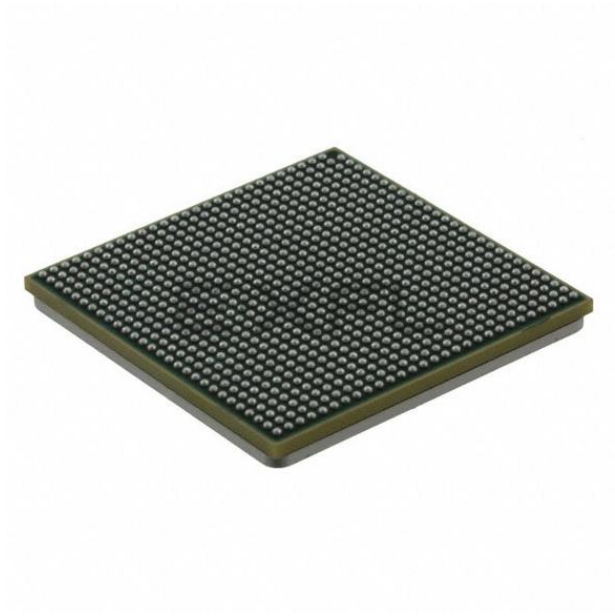

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	Signal Processing; SPE, Security; SEC
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8543ehxaqg

  - Up to 32 simultaneous open pages for DDR2
- Contiguous or discontiguous memory mapping
- Read-modify-write support for RapidIO atomic increment, decrement, set, and clear transactions
- Sleep mode support for self-refresh SDRAM
- On-die termination support when using DDR2
- Supports auto refreshing
- On-the-fly power management using CKE signal
- Registered DIMM support
- Fast memory access via JTAG port
- 2.5-V SSTL_2 compatible I/O (1.8-V SSTL_1.8 for DDR2)
- Support for battery-backed main memory

- Programmable interrupt controller (PIC)
  - Programming model is compliant with the OpenPIC architecture.
  - Supports 16 programmable interrupt and processor task priority levels
  - Supports 12 discrete external interrupts
  - Supports 4 message interrupts with 32-bit messages
  - Supports connection of an external interrupt controller such as the 8259 programmable interrupt controller
  - Four global high-resolution timers/counters that can generate interrupts
  - Supports a variety of other internal interrupt sources
  - Supports fully nested interrupt delivery
  - Interrupts can be routed to external pin for external processing.
  - Interrupts can be routed to the e500 core's standard or critical interrupt inputs.
  - Interrupt summary registers allow fast identification of interrupt source.
- Integrated security engine (SEC) optimized to process all the algorithms associated with IPSec, IKE, WTLS/WAP, SSL/TLS, and 3GPP
  - Four crypto-channels, each supporting multi-command descriptor chains
    - Dynamic assignment of crypto-execution units via an integrated controller
    - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
  - PKEU—public key execution unit
    - RSA and Diffie-Hellman; programmable field size up to 2048 bits
    - Elliptic curve cryptography with F_2m and F(p) modes and programmable field size up to 511 bits
  - DEU—Data Encryption Standard execution unit
    - DES, 3DES
    - Two key (K1, K2) or three key (K1, K2, K3)
    - ECB and CBC modes for both DES and 3DES

  - AESU—Advanced Encryption Standard unit
    - Implements the Rijndael symmetric key cipher
    - ECB, CBC, CTR, and CCM modes
    - 128-, 192-, and 256-bit key lengths
  - AFEU—ARC four execution unit
    - Implements a stream cipher compatible with the RC4 algorithm
    - 40- to 128-bit programmable key
  - MDEU—message digest execution unit
    - SHA with 160- or 256-bit message digest
    - MD5 with 128-bit message digest
    - HMAC with either algorithm
  - KEU—Kasumi execution unit
    - Implements F8 algorithm for encryption and F9 algorithm for integrity checking
    - Also supports A5/3 and GEA-3 algorithms
  - RNG—random number generator
  - XOR engine for parity checking in RAID storage applications
- Dual I^2C controllers
  - Two-wire interface
  - Multiple master support
  - Master or slave I^2C mode support
  - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
  - Optionally loads configuration data from serial ROM at reset via the I^2C interface
  - Can be used to initialize configuration registers and/or memory
  - Supports extended I^2C addressing mode
  - Data integrity checked with preamble signature and CRC
- DUART
  - Two 4-wire interfaces (SIN, SOUT, $\overline{\text{RTS}}$, $\overline{\text{CTS}}$)
  - Programming model compatible with the original 16450 UART and the PC16550D
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data bus operating at up to 133 MHz
  - Eight chip selects support eight external slaves
  - Up to eight-beat burst transfers
  - The 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller.
  - Three protocol engines available on a per chip select basis:
    - General-purpose chip select machine (GPCM)
    - Three user programmable machines (UPMs)

  - VRRP and HSRP support for seamless router fail-over
  - Up to 16 exact-match MAC addresses supported
  - Broadcast address (accept/reject)
  - Hash table match on up to 512 multicast addresses
  - Promiscuous mode
- Buffer descriptors backward compatible with MPC8260 and MPC860T 10/100 Ethernet programming models
- RMON statistics support
- 10-Kbyte internal transmit and 2-Kbyte receive FIFOs
- MII management interface for control and status
- Ability to force allocation of header information and buffer descriptors into L2 cache

- OCeaN switch fabric
  - Full crossbar packet switch
  - Reorders packets from a source based on priorities
  - Reorders packets to bypass blocked packets
  - Implements starvation avoidance algorithms
  - Supports packets with payloads of up to 256 bytes
- Integrated DMA controller
  - Four-channel controller
  - All channels accessible by both the local and remote masters
  - Extended DMA functions (advanced chaining and striding capability)
  - Support for scatter and gather transfers
  - Misaligned transfer capability
  - Interrupt on completed segment, link, list, and error
  - Supports transfers to or from any local memory or I/O port
  - Selectable hardware-enforced coherency (snoop/no snoop)
  - Ability to start and flow control each DMA channel from external 3-pin interface
  - Ability to launch DMA from single write transaction
- Two PCI/PCI-X controllers
  - PCI 2.2 and PCI-X 1.0 compatible
  - One 32-/64-bit PCI/PCI-X port with support for speeds of up to 133 MHz (maximum PCI-X frequency in synchronous mode is 110 MHz)
  - One 32-bit PCI port with support for speeds from 16 to 66 MHz (available when the other port is in 32-bit mode)
  - Host and agent mode support
  - 64-bit dual address cycle (DAC) support
  - PCI-X supports multiple split transactions
  - Supports PCI-to-memory and memory-to-PCI streaming

2.1.3 Output Driver Characteristics

The following table provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Programmable Output Impedance (Ω)	Supply Voltage	Notes
Local bus interface utilities signals	25 25	BV_{DD} = 3.3 V BV_{DD} = 2.5 V	1
	45(default) 45(default)	BV_{DD} = 3.3 V BV_{DD} = 2.5 V	
PCI signals	25	OV_{DD} = 3.3 V	2
	45(default)		
DDR signal	18 36 (half strength mode)	GV_{DD} = 2.5 V	3
DDR2 signal	18 36 (half strength mode)	GV_{DD} = 1.8 V	3
TSEC/10/100 signals	45	L/TV_{DD} = 2.5/3.3 V	—
DUART, system control, JTAG	45	OV_{DD} = 3.3 V	—
I2C	150	OV_{DD} = 3.3 V	—

Notes:

1. The drive strength of the local bus interface is determined by the configuration of the appropriate bits in PORIMPSCR.
2. The drive strength of the PCI interface is determined by the setting of the $\overline{\text{PCI\_GNT1}}$ signal at reset.
3. The drive strength of the DDR interface in half-strength mode is at T_j = 105°C and at GV_{DD} (min).

2.2 Power Sequencing

The device requires its power rails to be applied in a specific sequence in order to ensure proper device operation. These requirements are as follows for power-up:

1. V_{DD}, AV_{DD}_n, BV_{DD}, LV_{DD}, OV_{DD}, SV_{DD}, TV_{DD}, XV_{DD}
2. GV_{DD}

All supplies must be at their stable values within 50 ms.

NOTE

Items on the same line have no ordering requirement with respect to one another. Items on separate lines must be ordered sequentially such that voltage rails on a previous step must reach 90% of their value before the voltage rails on the current step reach 10% of theirs.

NOTE

In order to guarantee MCKE low during power-up, the above sequencing for GV_{DD} is required. If there is no concern about any of the DDR signals being in an indeterminate state during power-up, then the sequencing for GV_{DD} is not required.

3 Power Characteristics

The estimated typical power dissipation for the core complex bus (CCB) versus the core frequency for this family of PowerQUICC III devices is shown in the following table.

Table 4. Device Power Dissipation

CCB Frequency[1]	Core Frequency	SLEEP[2]	Typical-65[3]	Typical-105[4]	Maximum[5]	Unit
400	800	2.7	4.6	7.5	8.1	W
	1000	2.7	5.0	7.9	8.5	W
	1200	2.7	5.4	8.3	8.9	
500	1500	11.5	13.6	16.5	18.6	W
533	1333	6.2	7.9	10.8	12.8	W

Notes:

1. CCB frequency is the SoC platform frequency, which corresponds to the DDR data rate.
2. SLEEP is based on V_{DD} = 1.1 V, T_j = 65°C.
3. Typical-65 is based on V_{DD} = 1.1 V, T_j = 65°C, running Dhrystone.
4. Typical-105 is based on V_{DD} = 1.1 V, T_j = 105°C, running Dhrystone.
5. Maximum is based on V_{DD} = 1.1 V, T_j = 105°C, running a smoke test.

5 RESET Initialization

This section describes the AC electrical specifications for the RESET initialization timing requirements of the device. The following table provides the RESET initialization AC timing specifications for the DDR SDRAM component(s).

Table 8. RESET Initialization Timing Specifications

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$	100	—	μs	—
Minimum assertion time for $\overline{\text{SRESET}}$	3	—	SYSCLKs	1
PLL input setup time with stable SYSCLK before $\overline{\text{HRESET}}$ negation	100	—	μs	—
Input setup time for POR configs (other than PLL config) with respect to negation of $\overline{\text{HRESET}}$	4	—	SYSCLKs	1
Input hold time for all POR configs (including PLL config) with respect to negation of $\overline{\text{HRESET}}$	2	—	SYSCLKs	1
Maximum valid-to-high impedance time for actively driven POR configs with respect to negation of $\overline{\text{HRESET}}$	—	5	SYSCLKs	1

Note:

1. SYSCLK is the primary clock input for the device.

The following table provides the PLL lock times.

Table 9. PLL Lock Times

Parameter/Condition	Min	Max	Unit
Core and platform PLL lock times	—	100	μs
Local bus PLL lock time	—	50	μs
PCI/PCI-X bus PLL lock time	—	50	μs

5.1 Power-On Ramp Rate

This section describes the AC electrical specifications for the power-on ramp rate requirements. Controlling the maximum power-on ramp rate is required to avoid falsely triggering the ESD circuitry. The following table provides the power supply ramp rate specifications.

Table 10. Power Supply Ramp Rate

Parameter	Min	Max	Unit	Notes
Required ramp rate for MVREF	—	3500	V/s	1
Required ramp rate for VDD	—	4000	V/s	1, 2

Note:

1. Maximum ramp rate from 200 to 500 mV is most critical as this range may falsely trigger the ESD circuitry.
2. VDD itself is not vulnerable to false ESD triggering; however, as per Section 22.2, "PLL Power Supply Filtering," the recommended AVDD_CORE, AVDD_PLAT, AVDD_LBIU, AVDD_PCI1 and AVDD_PCI2 filters are all connected to VDD. Their ramp rates must be equal to or less than the VDD ramp rate.

Table 13 provides the recommended operating conditions for the DDR SDRAM controller when GV_{DD}(typ) = 2.5 V.

Table 13. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MV_{REF} + 0.15	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.15	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–16.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	16.2	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail must track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

Table 14 provides the DDR I/O capacitance when GV_{DD}(typ) = 2.5 V.

Table 14. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the current draw characteristics for MV_{REF}.

Table 15. Current Draw Characteristics for MV_{REF}

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

Note:
1. The voltage regulator for MV_{REF} must be able to supply up to 500 μA current.

10 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the device.

10.1 Local Bus DC Electrical Characteristics

This table provides the DC electrical characteristics for the local bus interface operating at BV_{DD} = 3.3 V DC.

Table 38. Local Bus DC Electrical Characteristics (3.3 V DC)

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN}[1] = 0 V or V_{IN} = BV_{DD})	I_{IN}	—	±5	μA
High-level output voltage (BV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V
Low-level output voltage (BV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1 and Table 2.

Table 39 provides the DC electrical characteristics for the local bus interface operating at BV_{DD} = 2.5 V DC.

Table 39. Local Bus DC Electrical Characteristics (2.5 V DC)

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	1.70	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.7	V
Input current (V_{IN}[1] = 0 V or V_{IN} = BV_{DD})	I_{IH}	—	10	μA
	I_{IL}		–15	
High-level output voltage (BV_{DD} = min, I_{OH} = –1 mA)	V_{OH}	2.0	—	V
Low-level output voltage (BV_{DD} = min, I_{OL} = 1 mA)	V_{OL}	—	0.4	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1 and Table 2.

Table 42. Local Bus Timing Parameters—PLL Bypassed (continued)

Parameter	Symbol[1]	Min	Max	Unit	Notes
$\overline{\text{LGTA}}$/LUPWAIT input hold from local bus clock	$t_{LBIXKL2}$	–1.3	—	ns	4, 5
LALE output transition to LAD/LDP output transition (LATCH hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKLOV1}$	—	–0.3	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKLOV2}$	—	–0.1	ns	4
Local bus clock to address valid for LAD	$t_{LBKLOV3}$	—	0	ns	4
Local bus clock to LALE assertion	$t_{LBKLOV4}$	—	0	ns	4
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKLOX1}$	–3.7	—	ns	4
Output hold from local bus clock for LAD/LDP	$t_{LBKLOX2}$	–3.7	—	ns	4
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKLOZ1}$	—	0.2	ns	7
Local bus clock to output high impedance for LAD/LDP	$t_{LBKLOZ2}$	—	0.2	ns	7

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to local bus clock for PLL bypass mode. Timings may be negative with respect to the local bus clock because the actual launch and capture of signals is done with the internal launch/capture clock, which precedes LCLK by t_{LBKHKT}.
3. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[*n*]. Skew measured between complementary signals at $BV_{DD}/2$.
4. All signals are measured from $BV_{DD}/2$ of the rising edge of local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 3.3-V signaling levels.
5. Input timings are measured at the pin.
6. The value of t_{LBOTOT} is the measurement of the minimum time between the negation of LALE and any change in LAD.
7. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
8. Guaranteed by characterization.
9. Guaranteed by design.

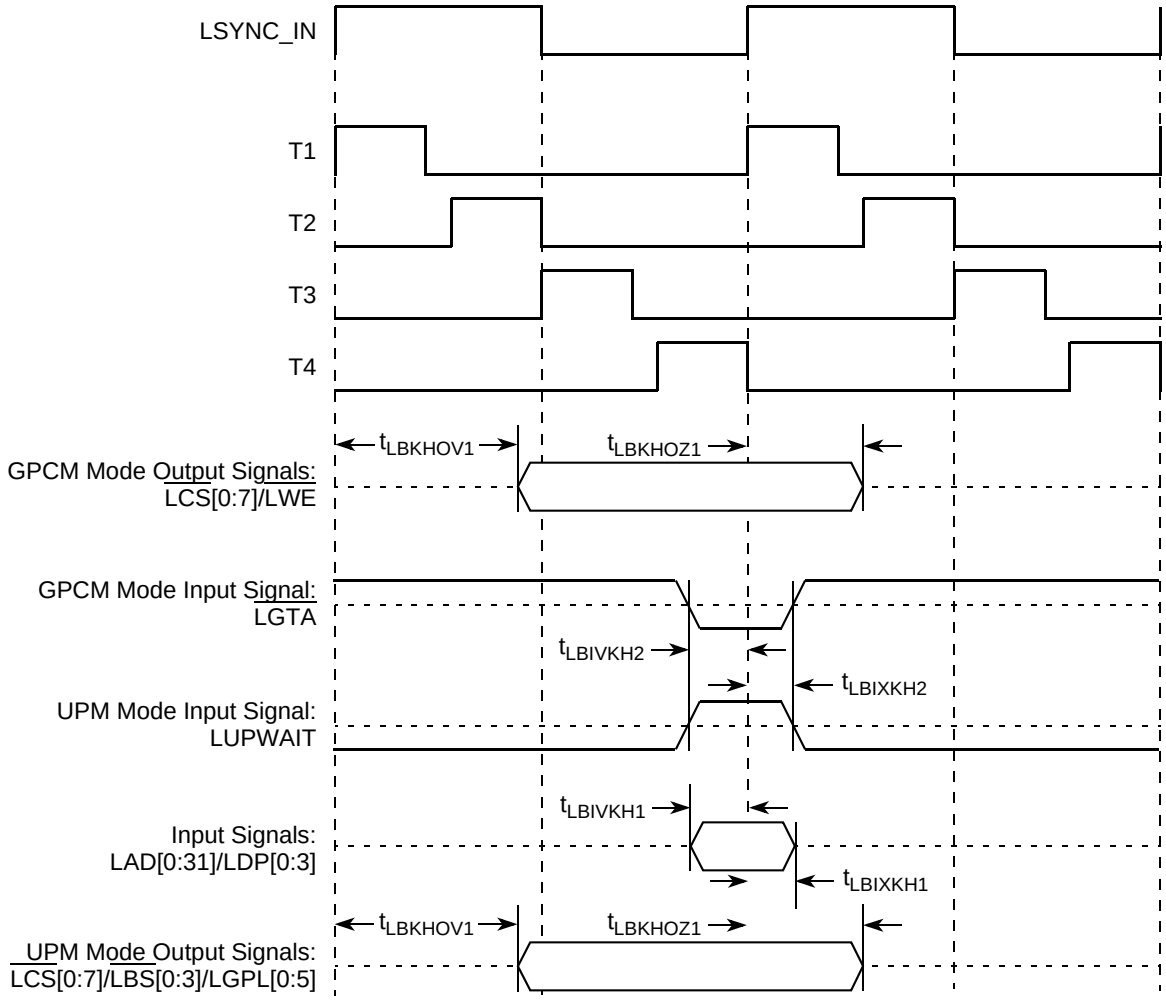

Figure 27. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 8 or 16 (PLL Enabled)

13 I²C

This section describes the DC and AC electrical characteristics for the I²C interfaces of the device.

13.1 I²C DC Electrical Characteristics

This table provides the DC electrical characteristics for the I²C interfaces.

Table 45. I²C DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	$OV_{DD} + 0.3$	V	—
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	$0.2 \times OV_{DD}$	V	1
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	2
Input current each I/O pin (input voltage is between $0.1 \times OV_{DD}$ and $0.9 \times OV_{DD}$(max)	I_I	–10	10	μA	3
Capacitance for each I/O pin	C_I	—	10	pF	—

Notes:

1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. See the *MPC8548E PowerQUICC™ III Integrated Processor Family Reference Manual*, for information on the digital filter used.
3. I/O pins obstruct the SDA and SCL lines if OV_{DD} is switched off.

13.2 I²C AC Electrical Specifications

This table provides the AC timing parameters for the I²C interfaces.

Table 46. I²C AC Electrical Specifications

Parameter	Symbol[1]	Min	Max	Unit	Notes
SCL clock frequency	f_{I2C}	0	400	kHz	—
Low period of the SCL clock	t_{I2CL}	1.3	—	μs	4
High period of the SCL clock	t_{I2CH}	0.6	—	μs	4
Setup time for a repeated START condition	t_{I2SVKH}	0.6	—	μs	4
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{I2SXKL}	0.6	—	μs	4
Data setup time	t_{I2DVKH}	100	—	ns	4
Data input hold time: CBUS compatible masters I²C bus devices	t_{I2DXKL}	 — 0	 — —	μs	2
Data output delay time:	t_{I2OVKL}	—	0.9	—	3
Set-up time for STOP condition	t_{I2PVKH}	0.6	—	μs	—
Bus free time between a STOP and START condition	t_{I2KHDX}	1.3	—	μs	—

Figure 36 shows the PCI/PCI-X input AC timing conditions.

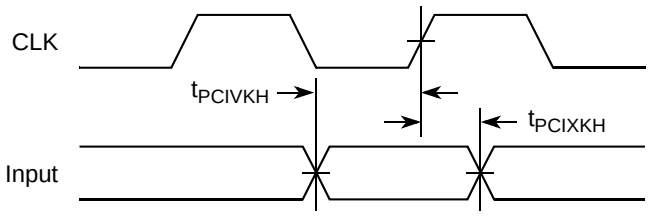

Figure 36. PCI/PCI-X Input AC Timing Measurement Conditions

Figure 37 shows the PCI/PCI-X output AC timing conditions.

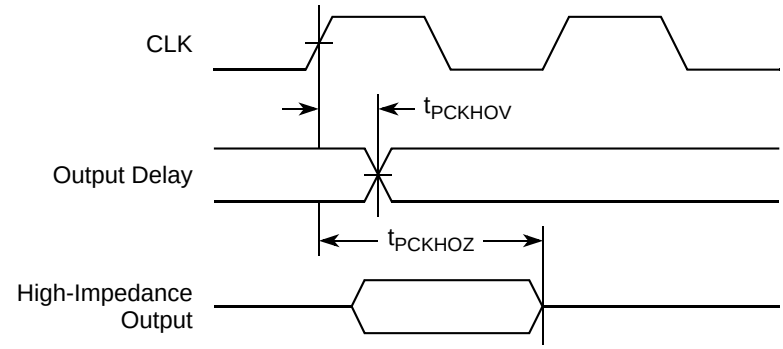

Figure 37. PCI/PCI-X Output AC Timing Measurement Condition

Table 53 provides the PCI-X AC timing specifications at 66 MHz.

Table 53. PCI-X AC Timing Specifications at 66 MHz

Parameter	Symbol	Min	Max	Unit	Notes
SYSCLK to signal valid delay	t_{PCKHOV}	—	3.8	ns	1, 2, 3, 7, 8
Output hold from SYSCLK	t_{PCKHOX}	0.7	—	ns	1, 10
SYSCLK to output high impedance	t_{PCKHOZ}	—	7	ns	1, 4, 8, 11
Input setup time to SYSCLK	t_{PCIVKH}	1.7	—	ns	3, 5
Input hold time from SYSCLK	t_{PCIXKH}	0.5	—	ns	10
$\overline{\text{REQ64}}$ to $\overline{\text{HRESET}}$ setup time	t_{PCRVRH}	10	—	clocks	11
$\overline{\text{HRESET}}$ to $\overline{\text{REQ64}}$ hold time	t_{PCRHRX}	0	50	ns	11
$\overline{\text{HRESET}}$ high to first $\overline{\text{FRAME}}$ assertion	t_{PCRHFV}	10	—	clocks	9, 11
PCI-X initialization pattern to $\overline{\text{HRESET}}$ setup time	t_{PCIVRH}	10	—	clocks	11

Table 72. MPC8547E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Local Bus Controller Interface				
LAD[0:31]	E27, B20, H19, F25, A20, C19, E28, J23, A25, K22, B28, D27, D19, J22, K20, D28, D25, B25, E22, F22, F21, C25, C22, B23, F20, A23, A22, E19, A21, D21, F19, B21	I/O	BV_{DD}	—
LDP[0:3]	K21, C28, B26, B22	I/O	BV_{DD}	—
LA[27]	H21	O	BV_{DD}	5, 9
LA[28:31]	H20, A27, D26, A28	O	BV_{DD}	5, 7, 9
$\overline{\text{LCS}}$[0:4]	J25, C20, J24, G26, A26	O	BV_{DD}	—
$\overline{\text{LCS5}}$/$\overline{\text{DMA\_DREQ2}}$	D23	I/O	BV_{DD}	1
$\overline{\text{LCS6}}$/$\overline{\text{DMA\_DACK2}}$	G20	O	BV_{DD}	1
$\overline{\text{LCS7}}$/$\overline{\text{DMA\_DDONE2}}$	E21	O	BV_{DD}	1
$\overline{\text{LWE0}}$/$\overline{\text{LBS0}}$/LSDDQM[0]	G25	O	BV_{DD}	5, 9
$\overline{\text{LWE1}}$/$\overline{\text{LBS1}}$/LSDDQM[1]	C23	O	BV_{DD}	5, 9
$\overline{\text{LWE2}}$/$\overline{\text{LBS2}}$/LSDDQM[2]	J21	O	BV_{DD}	5, 9
$\overline{\text{LWE3}}$/$\overline{\text{LBS3}}$/LSDDQM[3]	A24	O	BV_{DD}	5, 9
LALE	H24	O	BV_{DD}	5, 8, 9
LBCTL	G27	O	BV_{DD}	5, 8, 9
LGPL0/LSDA10	F23	O	BV_{DD}	5, 9
LGPL1/$\overline{\text{LSDWE}}$	G22	O	BV_{DD}	5, 9
LGPL2/$\overline{\text{LOE}}$/$\overline{\text{LSDRAS}}$	B27	O	BV_{DD}	5, 8, 9
LGPL3/$\overline{\text{LSDCAS}}$	F24	O	BV_{DD}	5, 9
LGPL4/$\overline{\text{LGTA}}$/LUPWAIT/LPBSE	H23	I/O	BV_{DD}	—
LGPL5	E26	O	BV_{DD}	5, 9
LCKE	E24	O	BV_{DD}	—
LCLK[0:2]	E23, D24, H22	O	BV_{DD}	—
LSYNC_IN	F27	I	BV_{DD}	—
LSYNC_OUT	F28	O	BV_{DD}	—
DMA				
$\overline{\text{DMA\_DACK}}$[0:1]	AD3, AE1	O	OV_{DD}	5, 9, 107
$\overline{\text{DMA\_DREQ}}$[0:1]	AD4, AE2	I	OV_{DD}	—
$\overline{\text{DMA\_DDONE}}$[0:1]	AD2, AD1	O	OV_{DD}	—
Programmable Interrupt Controller				
$\overline{\text{UDE}}$	AH16	I	OV_{DD}	—
$\overline{\text{MCP}}$	AG19	I	OV_{DD}	—

Table 73. MPC8545E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{SD\_TX}}$[0:3]	M23, N21, P23, R21	O	XV_{DD}	—
Reserved	W26, Y28, AA26, AB28	—	—	40
Reserved	W25, Y27, AA25, AB27	—	—	40
Reserved	U20, V22, W20, Y22	—	—	15
Reserved	U21, V23, W21, Y23	—	—	15
SD_PLL_TPD	U28	O	XV_{DD}	24
SD_REF_CLK	T28	I	XV_{DD}	—
$\overline{\text{SD\_REF\_CLK}}$	T27	I	XV_{DD}	—
Reserved	AC1, AC3	—	—	2
Reserved	M26, V28	—	—	32
Reserved	M25, V27	—	—	34
Reserved	M20, M21, T22, T23	—	—	38
General-Purpose Output				
GPOUT[24:31]	K26, K25, H27, G28, H25, J26, K24, K23	O	BV_{DD}	—
System Control				
$\overline{\text{HRESET}}$	AG17	I	OV_{DD}	—
$\overline{\text{HRESET\_REQ}}$	AG16	O	OV_{DD}	29
$\overline{\text{SRESET}}$	AG20	I	OV_{DD}	—
$\overline{\text{CKSTP\_IN}}$	AA9	I	OV_{DD}	—
$\overline{\text{CKSTP\_OUT}}$	AA8	O	OV_{DD}	2, 4
Debug				
TRIG_IN	AB2	I	OV_{DD}	—
TRIG_OUT/READY/$\overline{\text{QUIESCE}}$	AB1	O	OV_{DD}	6, 9, 19, 29
MSRCID[0:1]	AE4, AG2	O	OV_{DD}	5, 6, 9
MSRCID[2:4]	AF3, AF1, AF2	O	OV_{DD}	6, 19, 29
MDVAL	AE5	O	OV_{DD}	6
CLK_OUT	AE21	O	OV_{DD}	11
Clock				
RTC	AF16	I	OV_{DD}	—
SYSCLK	AH17	I	OV_{DD}	—
JTAG				
TCK	AG28	I	OV_{DD}	—
TDI	AH28	I	OV_{DD}	12

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{MWE}}$	E7	O	GV_{DD}	—
$\overline{\text{MCAS}}$	H7	O	GV_{DD}	—
$\overline{\text{MRAS}}$	L8	O	GV_{DD}	—
MCKE[0:3]	F10, C10, J11, H11	O	GV_{DD}	11
$\overline{\text{MCS}}$[0:3]	K8, J8, G8, F8	O	GV_{DD}	—
MCK[0:5]	H9, B15, G2, M9, A14, F1	O	GV_{DD}	—
$\overline{\text{MCK}}$[0:5]	J9, A15, G1, L9, B14, F2	O	GV_{DD}	—
MODT[0:3]	E6, K6, L7, M7	O	GV_{DD}	—
MDIC[0:1]	A19, B19	I/O	GV_{DD}	36
Local Bus Controller Interface				
LAD[0:31]	E27, B20, H19, F25, A20, C19, E28, J23, A25, K22, B28, D27, D19, J22, K20, D28, D25, B25, E22, F22, F21, C25, C22, B23, F20, A23, A22, E19, A21, D21, F19, B21	I/O	BV_{DD}	—
LDP[0:3]	K21, C28, B26, B22	I/O	BV_{DD}	—
LA[27]	H21	O	BV_{DD}	5, 9
LA[28:31]	H20, A27, D26, A28	O	BV_{DD}	5, 7, 9
$\overline{\text{LCS}}$[0:4]	J25, C20, J24, G26, A26	O	BV_{DD}	—
$\overline{\text{LCS5}}$/$\overline{\text{DMA\_DREQ2}}$	D23	I/O	BV_{DD}	1
$\overline{\text{LCS6}}$/$\overline{\text{DMA\_DACK2}}$	G20	O	BV_{DD}	1
$\overline{\text{LCS7}}$/$\overline{\text{DMA\_DDONE2}}$	E21	O	BV_{DD}	1
$\overline{\text{LWE0}}$/$\overline{\text{LBS0}}$/LSDDQM[0]	G25	O	BV_{DD}	5, 9
$\overline{\text{LWE1}}$/$\overline{\text{LBS1}}$/LSDDQM[1]	C23	O	BV_{DD}	5, 9
$\overline{\text{LWE2}}$/$\overline{\text{LBS2}}$/LSDDQM[2]	J21	O	BV_{DD}	5, 9
$\overline{\text{LWE3}}$/$\overline{\text{LBS3}}$/LSDDQM[3]	A24	O	BV_{DD}	5, 9
LALE	H24	O	BV_{DD}	5, 8, 9
LBCTL	G27	O	BV_{DD}	5, 8, 9
LGPL0/LSDA10	F23	O	BV_{DD}	5, 9
LGPL1/$\overline{\text{LSDWE}}$	G22	O	BV_{DD}	5, 9
LGPL2/$\overline{\text{LOE}}$/$\overline{\text{LSDRAS}}$	B27	O	BV_{DD}	5, 8, 9
LGPL3/$\overline{\text{LSDCAS}}$	F24	O	BV_{DD}	5, 9
LGPL4/$\overline{\text{LGTA}}$/LUPWAIT/LPBSE	H23	I/O	BV_{DD}	—
LGPL5	E26	O	BV_{DD}	5, 9
LCKE	E24	O	BV_{DD}	—
LCLK[0:2]	E23, D24, H22	O	BV_{DD}	—

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GPOUT[0:5]	N9, N10, P8, N7, R9, N5	O	LV_{DD}	—
cfg_dram_type0/GPOUT6	R8	O	LV_{DD}	5, 9
GPOUT7	N6	O	LV_{DD}	—
Reserved	P1	—	—	104
Reserved	R6	—	—	104
Reserved	P6	—	—	15
Reserved	N4	—	—	105
FIFO1_RXC2	P5	I	LV_{DD}	104
Reserved	R1	—	—	104
Reserved	P10	—	—	105
FIFO1_TXC2	P7	O	LV_{DD}	15
cfg_dram_type1	R10	O	LV_{DD}	5, 9
Three-Speed Ethernet Controller (Gigabit Ethernet 3)				
TSEC3_TXD[3:0]	V8, W10, Y10, W7	O	TV_{DD}	5, 9, 29
TSEC3_RXD[3:0]	Y1, W3, W5, W4	I	TV_{DD}	—
TSEC3_GTX_CLK	W8	O	TV_{DD}	—
TSEC3_RX_CLK	W2	I	TV_{DD}	—
TSEC3_RX_DV	W1	I	TV_{DD}	—
TSEC3_RX_ER	Y2	I	TV_{DD}	—
TSEC3_TX_CLK	V10	I	TV_{DD}	—
TSEC3_TX_EN	V9	O	TV_{DD}	30
TSEC3_TXD[7:4]	AB8, Y7, AA7, Y8	O	TV_{DD}	5, 9, 29
TSEC3_RXD[7:4]	AA1, Y3, AA2, AA4	I	TV_{DD}	—
Reserved	AA5	—	—	15
TSEC3_COL	Y5	I	TV_{DD}	—
TSEC3_CRS	AA3	I/O	TV_{DD}	31
TSEC3_TX_ER	AB6	O	TV_{DD}	—
DUART				
$\overline{\text{UART\_CTS}}$[0:1]	AB3, AC5	I	OV_{DD}	—
$\overline{\text{UART\_RTS}}$[0:1]	AC6, AD7	O	OV_{DD}	—
UART_SIN[0:1]	AB5, AC7	I	OV_{DD}	—
UART_SOUT[0:1]	AB7, AD8	O	OV_{DD}	—
I^2C interface				
IIC1_SCL	AG22	I/O	OV_{DD}	4, 27

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
TV_{DD}	W9, Y6	Power for TSEC3 and TSEC4 (2,5 V, 3.3 V)	TV_{DD}	—
GV_{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V,2.5 V)	GV_{DD}	—
BV_{DD}	C21, C24, C27, E20, E25, G19, G23, H26, J20	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV_{DD}	—
V_{DD}	M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19	Power for core (1.1 V)	V_{DD}	—
SV_{DD}	L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27	Core power for SerDes transceivers (1.1 V)	SV_{DD}	—
XV_{DD}	L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20	Pad power for SerDes transceivers (1.1 V)	XV_{DD}	—
AVDD_LBIU	J28	Power for local bus PLL (1.1 V)	—	26
AVDD_PCI1	AH21	Power for PCI1 PLL (1.1 V)	—	26
AVDD_PCI2	AH22	Power for PCI2 PLL (1.1 V)	—	26
AVDD_CORE	AH15	Power for e500 PLL (1.1 V)	—	26
AVDD_PLAT	AH19	Power for CCB PLL (1.1 V)	—	26
AVDD_SRDS	U25	Power for SRDSPLL (1.1 V)	—	26
SENSEVDD	M14	O	V_{DD}	13

Table 80. Memory Bus Clocking Specifications (MPC8543E)

Characteristic	Maximum Processor Core Frequency		Unit	Notes
	800, 1000 MHz			
	Min	Max		
Memory bus clock speed	166	200	MHz	1, 2

Notes:

1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies. See Section 20.2, "CCB/SYSCLK PLL Ratio," and Section 20.3, "e500 Core PLL Ratio," for ratio settings.
2. The memory bus speed is half of the DDR/DDR2 data rate, hence, half of the platform clock frequency.

20.2 CCB/SYSCLK PLL Ratio

The CCB clock is the clock that drives the e500 core complex bus (CCB), and is also called the platform clock. The frequency of the CCB is set using the following reset signals, as shown in Table 81:

- SYSCLK input signal
- Binary value on LA[28:31] at power up

Note that there is no default for this PLL ratio; these signals must be pulled to the desired values. Also note that the DDR data rate is the determining factor in selecting the CCB bus frequency, since the CCB frequency must equal the DDR data rate.

For specifications on the PCI_CLK, see the *PCI 2.2 Specification*.

Table 81. CCB Clock Ratio

Binary Value of LA[28:31] Signals	CCB:SYSCLK Ratio	Binary Value of LA[28:31] Signals	CCB:SYSCLK Ratio
0000	16:1	1000	8:1
0001	Reserved	1001	9:1
0010	2:1	1010	10:1
0011	3:1	1011	Reserved
0100	4:1	1100	12:1
0101	5:1	1101	20:1
0110	6:1	1110	Reserved
0111	Reserved	1111	Reserved

20.3 e500 Core PLL Ratio

This table describes the clock ratio between the e500 core complex bus (CCB) and the e500 core clock. This ratio is determined by the binary value of LBCTL, LALE, and LGPL2 at power up, as shown in this table.

Table 82. e500 Core to CCB Clock Ratio

Binary Value of LBCTL, LALE, LGPL2 Signals	e500 core:CCB Clock Ratio	Binary Value of LBCTL, LALE, LGPL2 Signals	e500 core:CCB Clock Ratio
000	4:1	100	2:1
001	9:2	101	5:2
010	Reserved	110	3:1
011	3:2	111	7:2

20.4 Frequency Options

Table 83This table shows the expected frequency values for the platform frequency when using a CCB clock to SYSCLK ratio in comparison to the memory bus clock speed.

Table 83. Frequency Options of SYSCLK with Respect to Memory Bus Speeds

CCB to SYSCLK Ratio	SYSCLK (MHz)								
	16.66	25	33.33	41.66	66.66	83	100	111	133.33
	Platform/CCB Frequency (MHz)								
2									
3								333	400
4						333	400	445	533
5					333	415	500		
6					400	500			
8				333	533				
9				375					
10			333	417					
12			400	500					
16		400	533						
20	333	500							

Note: Due to errata Gen 13 the max sys clk frequency must not exceed 100 MHz if the core clk frequency is below 1200 MHz.

21 Thermal

This section describes the thermal specifications of the device.

21.1 Thermal for Version 2.0 Silicon HiCTE FC-CBGA with Full Lid

This section describes the thermal specifications for the HiCTE FC-CBGA package for revision 2.0 silicon.

This table shows the package thermal characteristics.

Table 84. Package Thermal Characteristics for HiCTE FC-CBGA

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Die junction-to-ambient (natural convection)	Single-layer board (1s)	$R_{\theta JA}$	17	°C/W	1, 2
Die junction-to-ambient (natural convection)	Four-layer board (2s2p)	$R_{\theta JA}$	12	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Single-layer board (1s)	$R_{\theta JA}$	11	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Four-layer board (2s2p)	$R_{\theta JA}$	8	°C/W	1, 2
Die junction-to-board	N/A	$R_{\theta JB}$	3	°C/W	3
Die junction-to-case	N/A	$R_{\theta JC}$	0.8	°C/W	4

Notes:

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, airflow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-6 with the board (JESD51-7) horizontal.
3. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
4. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1). The cold plate temperature is used for the case temperature, measured value includes the thermal resistance of the interface layer.

21.2 Thermal for Version 2.1.1, 2.1.2, and 2.1.3 Silicon FC-PBGA with Full Lid and Version 3.1.x Silicon with Stamped Lid

This section describes the thermal specifications for the FC-PBGA package for revision 2.1.1, 2.1.2, and 3.0 silicon.

This table shows the package thermal characteristics.

Table 85. Package Thermal Characteristics for FC-PBGA

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Die junction-to-ambient (natural convection)	Single-layer board (1s)	$R_{\theta JA}$	18	°C/W	1, 2
Die junction-to-ambient (natural convection)	Four-layer board (2s2p)	$R_{\theta JA}$	13	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Single-layer board (1s)	$R_{\theta JA}$	13	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Four-layer board (2s2p)	$R_{\theta JA}$	9	°C/W	1, 2